

ABSTRACT

Disclosed are a semiconductor structure and a manufacturing method therefor. The semiconductor structure includes bit lines, wherein the bit lines extend in a first direction and are spaced apart from each other in a second direction, and the first direction intersects the
5 second direction; shield lines that are each located between two adjacent bit lines, extend in the first direction, and are arranged alternately with the bit lines in the second direction; active pillars, where the active pillars are located on the bit lines and arranged in an array in the first direction and the second direction; and bit line contact structures that are located between the bit lines and the active pillars and connect the bit lines and the active pillars, where a width
10 of each bit line contact structure in the second direction is less than widths of each bit line and each active pillar in the second direction.

[FIG. 2]